

Notification about the transfer of the semiconductor business

The semiconductor business of Panasonic Corporation was transferred on September 1, 2020 to Nuvoton Technology Corporation (hereinafter referred to as "Nuvoton"). Accordingly, Panasonic Semiconductor Solutions Co., Ltd. became under the umbrella of the Nuvoton Group, with the new name of Nuvoton Technology Corporation Japan (hereinafter referred to as "NTCJ").

In accordance with this transfer, semiconductor products will be handled as NTCJ-made products after September 1, 2020. However, such products will be continuously sold through Panasonic Corporation.

Publisher of this Document is NTCJ.

If you would find description "Panasonic" or "Panasonic semiconductor solutions", please replace it with NTCJ.

※ Except below description page

"Request for your special attention and precautions in using the technical information and semiconductors described in this book"

Nuvoton Technology Corporation Japan

FC5913010R

Dual N-channel MOSFET

For switching

■ Features

- Low drive voltage: 2.5 V drive
- Halogen-free / RoHS compliant
(EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol: V3

■ Basic Part Number

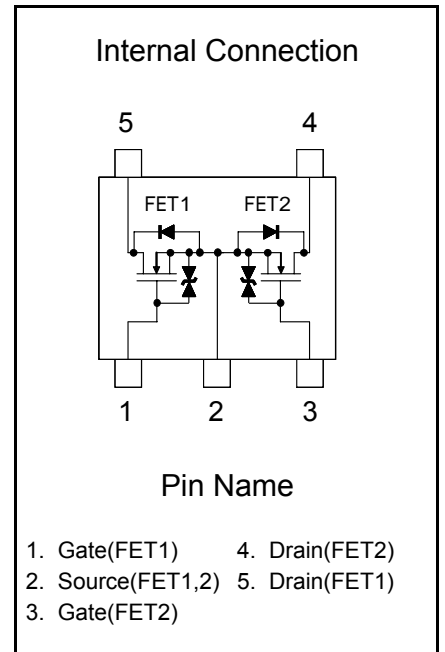
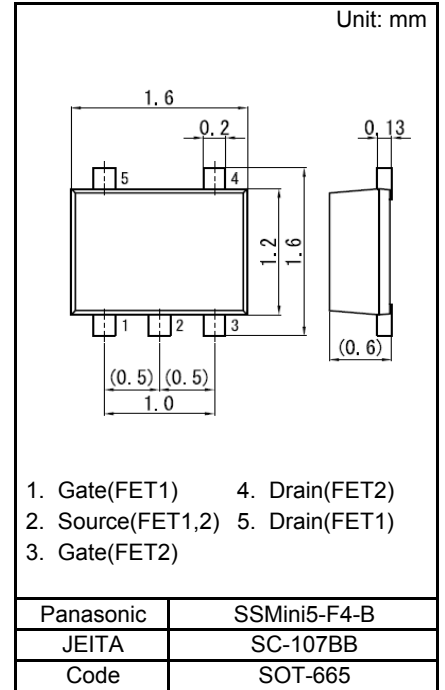
Dual FK330301 (Source Common type)

■ Packaging

FC5913010R Embossed type (Thermo-compression sealing):
8 000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25\text{ }^\circ\text{C}$

| Parameter | | Symbol | Rating | Unit |
|-----------|-------------------------|--------|--------------|------------------|
| FET1 | Drain-source Voltage | VDS | 30 | V |
| | Gate-source Voltage | VGS | ± 12 | V |
| FET2 | Drain Current | ID | 100 | mA |
| | Drain Current(Pulsed) | IDp | 200 | mA |
| Overall | Total Power dissipation | PD | 125 | mW |
| | Channel Temperature | Tch | 150 | $^\circ\text{C}$ |
| | Storage Temperature | Tstg | - 55 to +150 | $^\circ\text{C}$ |



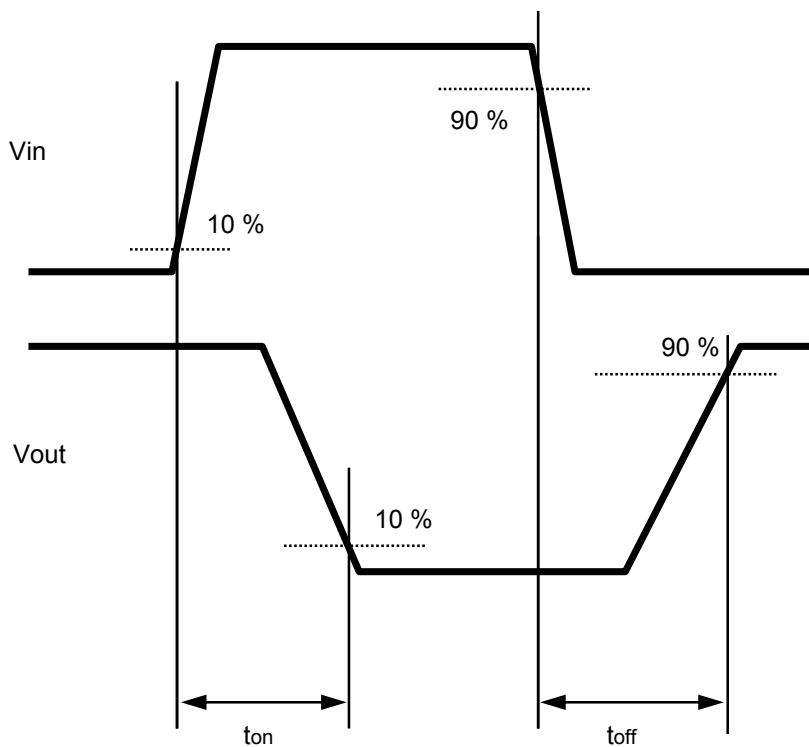
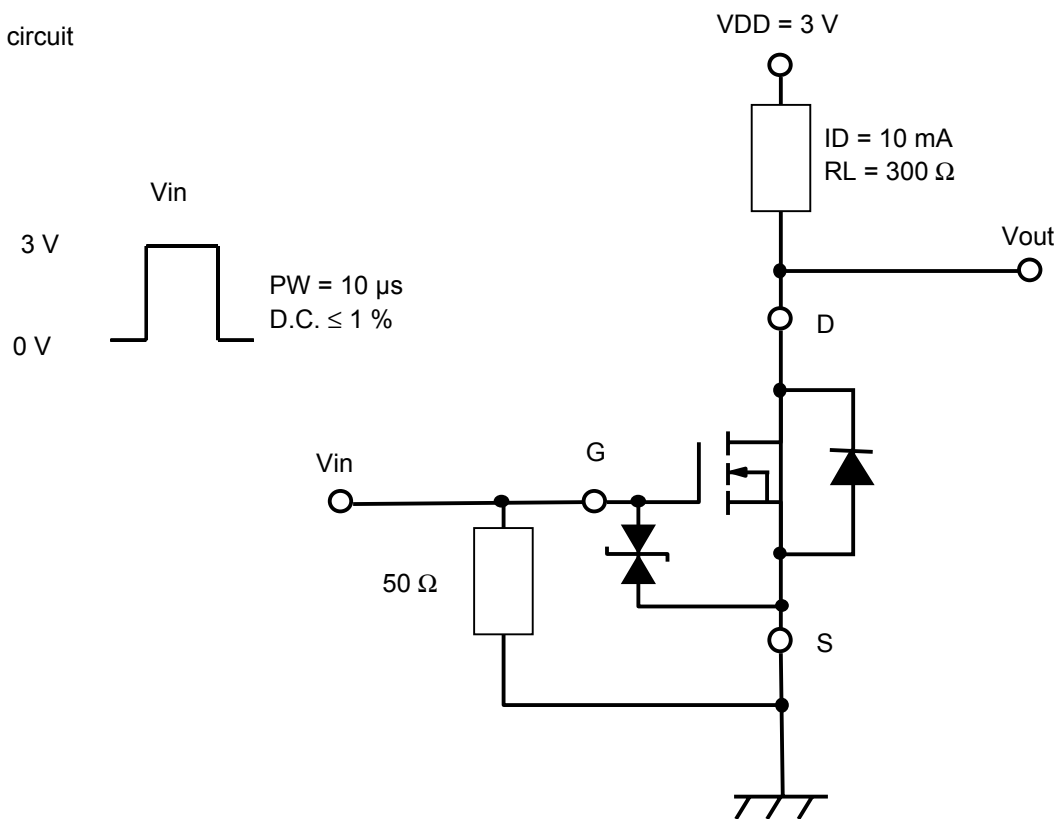
■ Electrical Characteristics Ta = 25 °C ± 3 °C
FET1,FET2

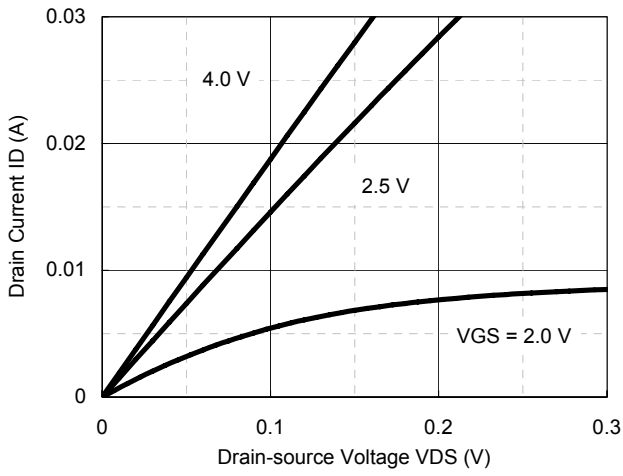
| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|----------------------------------|----------|---|-----|-----|-----|------|
| Drain-source Breakdown Voltage | VDSS | ID = 1 mA, VGS = 0 V | 30 | | | V |
| Zero Gate Voltage Drain Current | IDSS | VDS = 30 V, VGS = 0 V | | | 1.0 | μA |
| Gate-source Leakage Current | IGSS | VGS = ±10 V, VDS = 0 V | | | ±10 | μA |
| Gate-source Threshold Voltage | Vth | ID = 1.0 μA, VDS = 3.0 V | 0.5 | 1.0 | 1.5 | V |
| Drain-source On-state Resistance | RDS(on)1 | ID = 10 mA, VGS = 2.5 V | | 3 | 6 | Ω |
| | RDS(on)2 | ID = 10 mA, VGS = 4.0 V | | 2 | 3 | |
| Forward transfer admittance | Yfs | ID = 10 mA, VDS = 3.0 V | 20 | 55 | | S |
| Input Capacitance | Ciss | VDS = 3 V, VGS = 0 V, f = 1 MHz | | 12 | | pF |
| Output Capacitance | Coss | | | 7 | | |
| Reverse Transfer Capacitance | Crss | | | 3 | | |
| Turn-on time *1 | ton | VDD = 3 V, VGS = 0 V to 3 V ID = 10 mA | | 100 | | ns |
| Turn-off time *1 | toff | VDD = 3 V, VGS = 3 V to 0 V ID = 10 mA | | 100 | | ns |

Note: Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

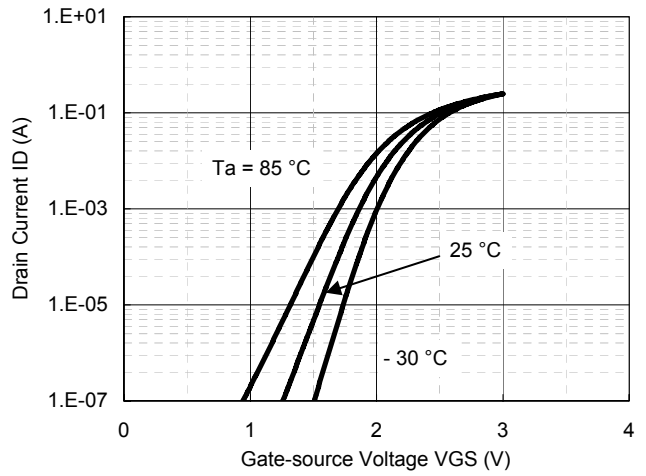
*1 See Test circuit.

*1 Test circuit

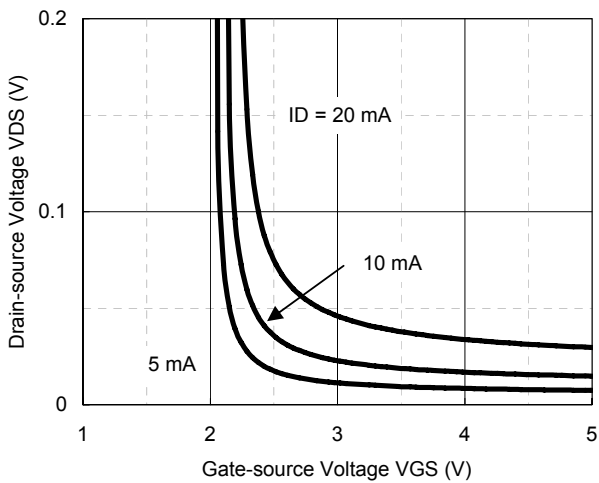




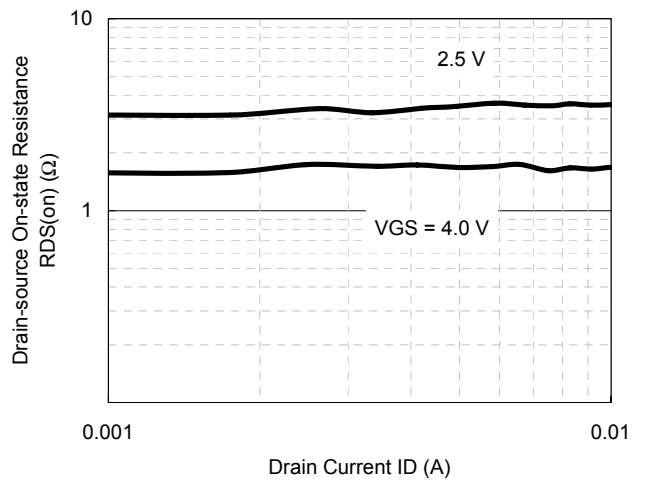
ID - VDS



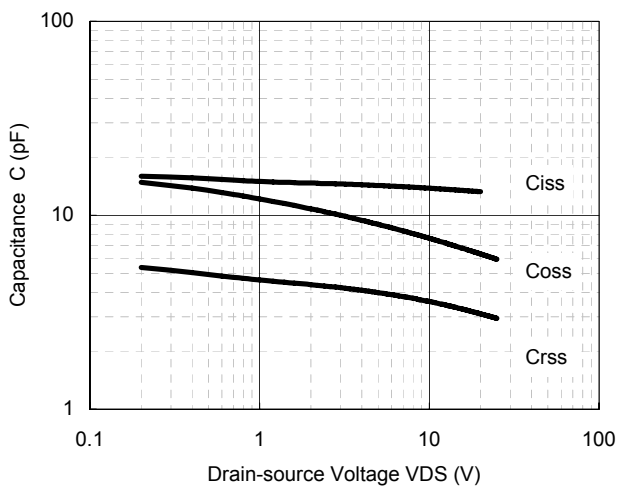
ID - VGS



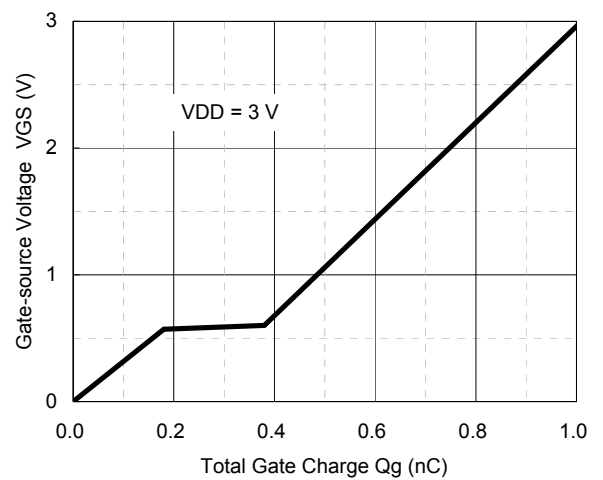
VDS - VGS



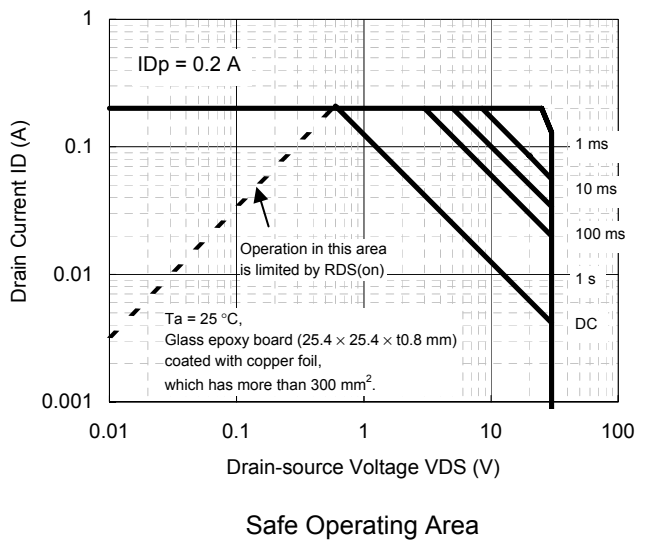
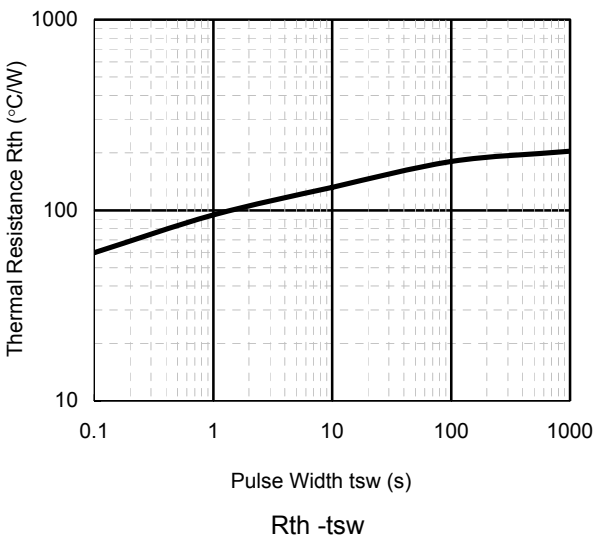
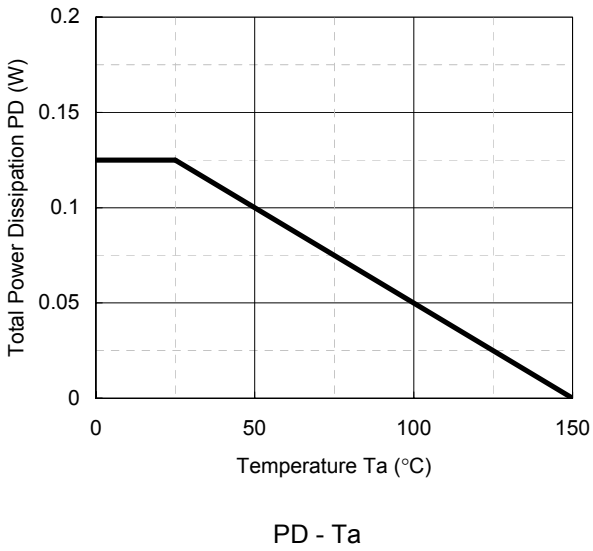
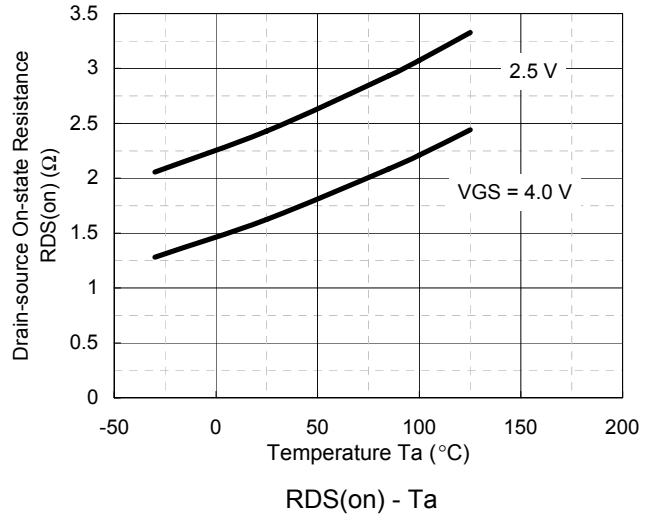
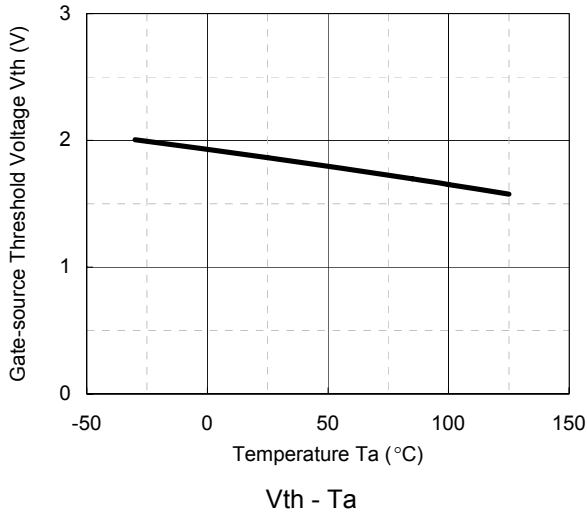
RDS(on) - ID



Capacitance - VDS

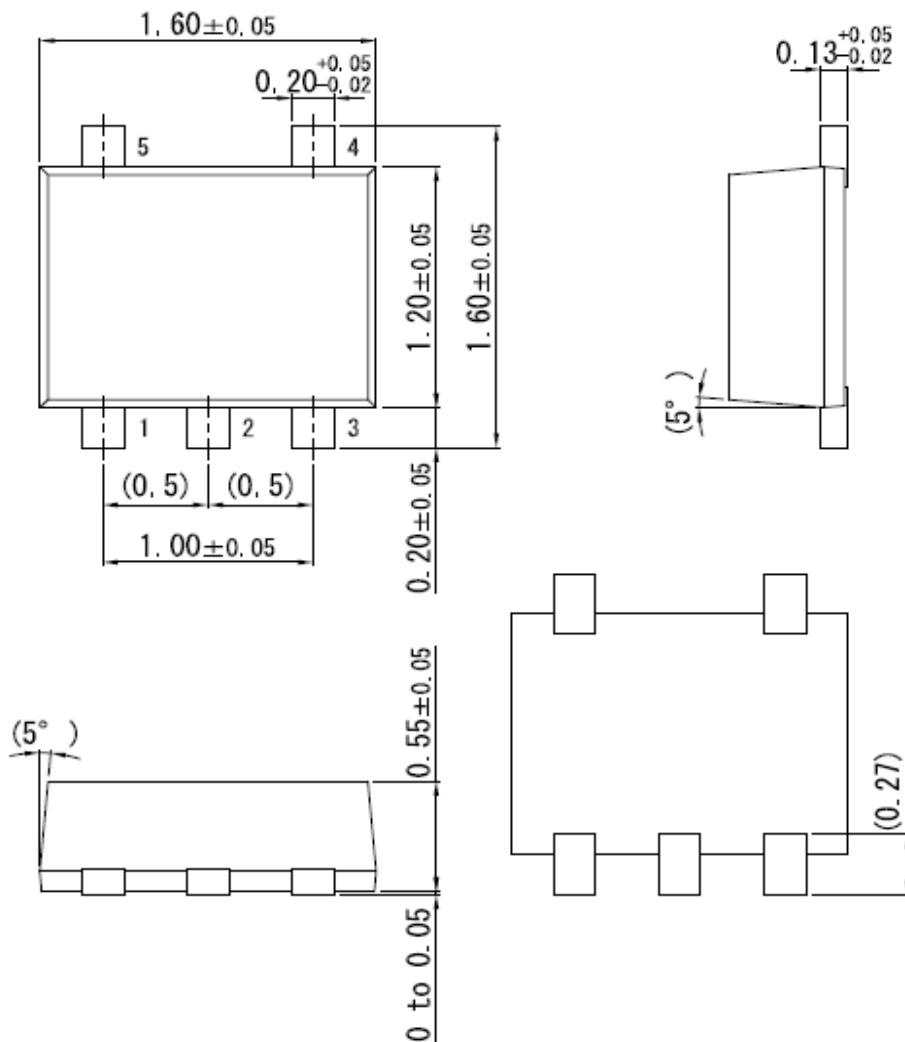


Dynamic Input/Output Characteristics

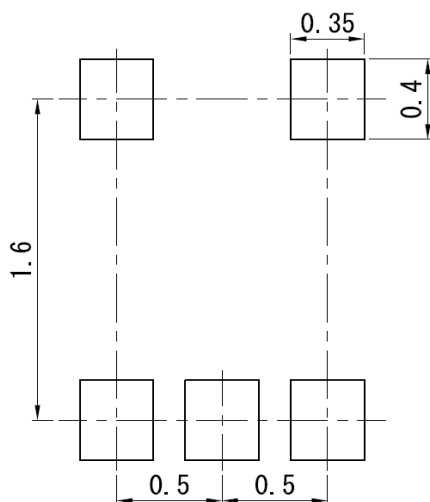


SSMini5-F4-B

Unit: mm



■ Land Pattern (Reference) (Unit: mm)



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